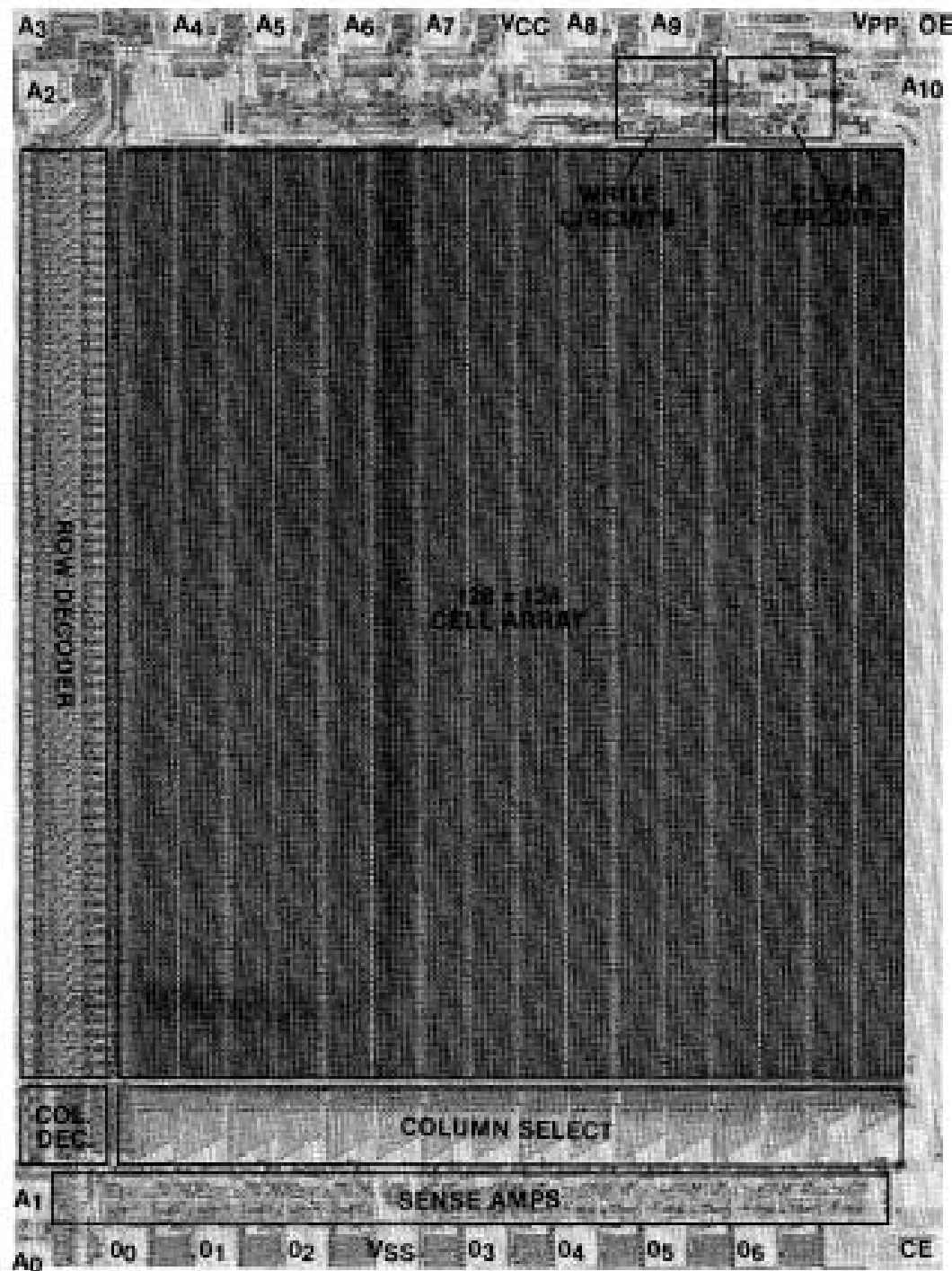


# FIRST 16KB FLOTOX EEPROM

*ISSCC 1980*



## A 16KB Electrically Erasable Nonvolatile Memory

IN 1980, JOHNSON et al. (Intel) described an electrically erasable nonvolatile memory. This device used a Floating Gate Tunnel Oxide (FLOTOX) two transistor cell. The cell size was  $0.85 \text{ mil}^2$  using  $3.5 \text{ }\mu\text{m}$  technology. Tunnel oxide thickness was less than 200 Angstrom, and endurance of more than  $10^5$  cycles was reported. This cell and the design techniques were widely adopted by the industry on many other memories.